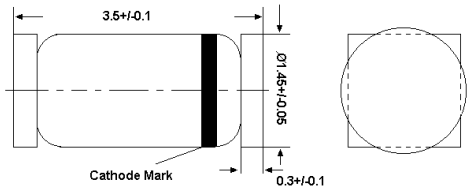
LS4150

Silicon Epitaxial Planar Switching Diode

Applications

• High speed switch and general
purpose use in com-puter and industrial applications

LS-34



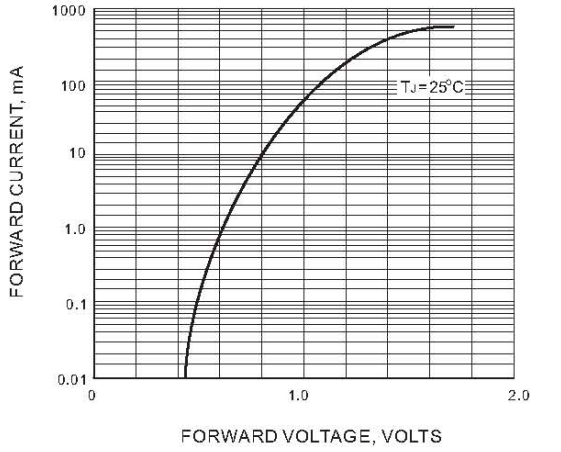
QuadroMELF
Dimensions in mm

Absolute Maximum Ratings (T_a = 25℃)

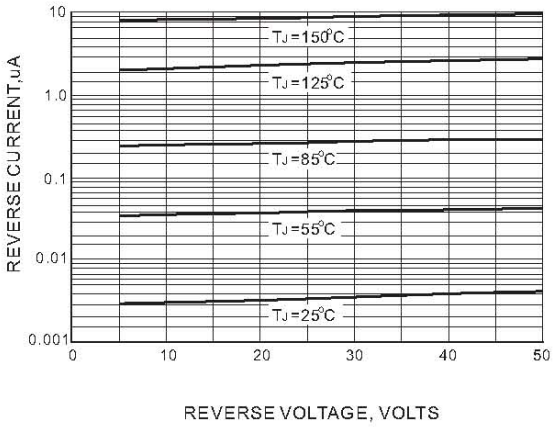
Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	50	V
Reverse Voltage	V_R	50	V
Average Rectified Forward Current	$I_{F(AV)}$	300	mA
Peak Forward Current	I_{FM}	600	mA
Non-Repetitive Peak Forward Surge Current (at t = 1 μs)	I_{FSM}	4	A
Power Dissipation	P_{tot}	500	mW
Junction temperature	T_j	175	℃
Storage Temperature Range	T_{stg}	- 65 to +175	℃

Characteristics at T_a = 25℃

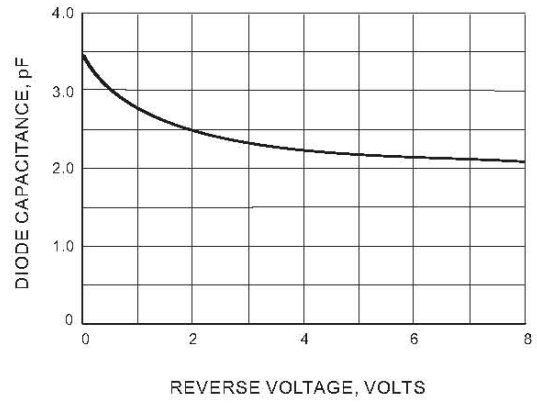
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 50 mA at I_F = 100 mA at I_F = 200 mA	V_F	 0.54 0.66 0.76 0.82 0.87	 0.62 0.74 0.86 0.92 1	V
Reverse Current at V_R = 50 V at V_R = 50 V, T_j = 150℃	I_R	 - -	 100 100	 nA μA
Capacitance at V_R = 0, f = 1 MHz	C_{tot}	-	4	pF
Reverse Recovery Time at I_F = 10 mA to I_R = 1 mA, I_{rr} = 0.1 x I_R , V_R = 6 V, R_L = 100 Ω	t_{rr}	-	4	ns



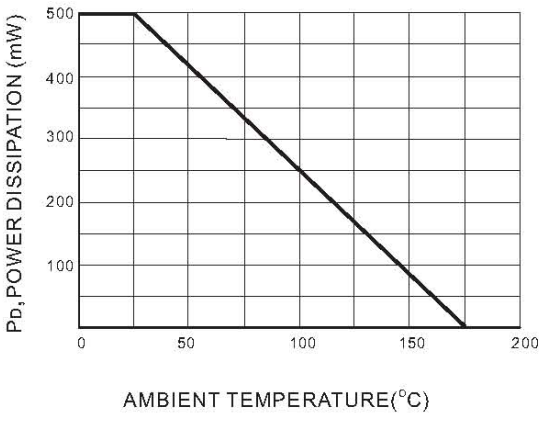
FORWARD VOLTAGE



LEAKAGE CURRENT



TYPICAL CAPATICANCE



POWER DERATING